

Tungsten and Other Refractory Metals for VLSI Applications III

EDITOR

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Preface

The ongoing evolution in the microelectronics industry is placing increasingly greater demands on the materials used in the interconnect technology. There is a need to provide greater reliability without impacting the electrical performance. At the same time the manufacturing methods must be capable of meeting the industrial needs of thruput, cost, yield, etc. if the process is to become accepted.

At this workshop, it is apparent that refractory materials have a place in the fabrication of VLSI circuits. First extensive investigations are being conducted to understand the materials and their interaction with silicon. Secondly, the process dynamics and methods are becoming better understood. Finally, the work on reliability and device structures show the advantages which these materials offer.

This volume is in the Materials Research Society series which was created to document the proceedings of this workshop. It contains fifty three papers which were presented at the Fourth Workshop on Tungsten and Other Refractory Metals for VLSI Applications. This workshop was held October 7-9, 1987 in Yorktown Heights, New York.

Future workshops on tungsten and other refractory metals will continue to be held in the fall of each year. Information on the date and location of upcoming workshops can be obtained from Ms. Linda Reid, University Extension, University of California, Berkley, (415) 642-4151, who is in charge of workshop administration.

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December 1987

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